M5M29GB/T320VP-80

33,554,432-BIT (4,194,304-WORD BY 8-BIT / 2,097,152-WORD BY16-BIT)
CMOS 3.3V-ONLY, BLOCK ERASE FLASH MEMORY

DESCRIPTION

The Mobile FLASH M5M29GB/T320VP are 3.3V-only high speed 33,554,432-bit CMOS boot block Flash Memories with alternating BGO (Back Ground Operation) feature. The BGO feature of the device allows Program or Erase operations to be performed in one bank while the device simultaneously allows Read operations to be performed on the other bank. This BGO feature is suitable for mobile and personal computing, and communication products. The M5M29GB/T320VP are fabricated by CMOS technology for the peripheral circuits and DINOR(Divided bit line NOR) architecture for the memory cells, and are available in 48pin TSOP(I).

FEATURES

Organization	2,097,152 word x 16bit
	4,194,304 word x 8 bit
Supply voltage	Vcc = 2.7 ~ 3.6V
A	00 () (0.0.00)
Access time	80ns (Vcc=3.0~3.6V)
Dower Discinction	90ns (Vcc=2.7~3.6V)
Power Dissipation Read	
Neau	12 IIIVV (IVIAX. at SIVII 12)
(After Automatic Power sa	aving) ······ 0.33µW (typ.)
Program/Erase ······	
	······ 0.33μW (typ.)
Deep power down mode	
Auto program for Bank(I) and	l Bank(II)
Program Time	4ms (typ.)
Program Unit	
(Byte Program) ······	····· 1word/1byte
	128word/256byte
 Auto program for Bank(III) ar 	nd Bank(IV)
	4ms (typ.)
	128word/256byte
Auto Erase	1201101012000910
	40 ms (typ.)
Erase Unit	40 m3 (typ.)
	4Kword/8Kbyte x 2
Darik(I) Door block	ock ······ 4Kword/8Kbyte x 6
Main Block ··	
IVIAITI DIOCK	32KWOIU/64KDyle X /
Bank(II) Main Block ··	
Bank(III) Main Block ··	32Kword/64Kbyte x 24
Bank(IV) Main Block ··	32Kword/64Kbyte x 24
• Brogram/Erasa avalos	100Kcycles
 Program/Erase cycles 	Tourcycles

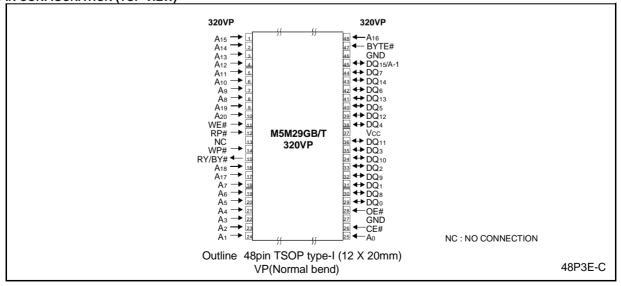
 Boot Block 	
M5M29GB320VP	·····Bottom Boot
M5M29GT320VP	Top Boot

- Other Functions
 Soft Ware Command Control
 Selective Block Lock
 Status Register Read
 - Alternating Back Ground Program/Erase Operation Between Bank(I) ,Bank(II),Bank(III) and Bank(IV)
- Package 48-Lead, 12mm x 20mm TSOP (type-I)

APPLICATION

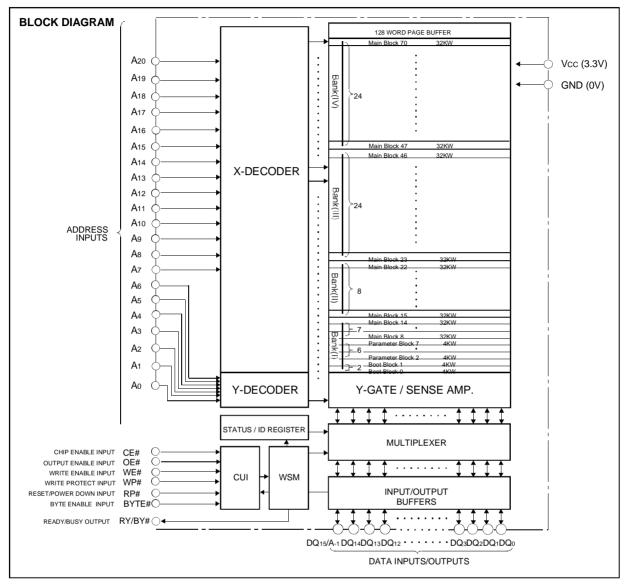
Code Strage
Digital Cellular Phone
Telecommunication
Mobile Computing Machine
PDA (Personal Digital Assistance)
Car Navigation System
Video Game Machine

PIN CONFIGURATION (TOP VIEW)

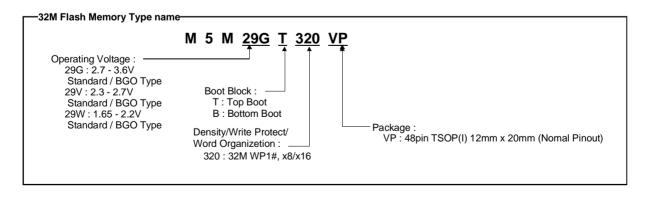


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CMOS 3.3V-ONLY, BLOCK ERASE FLASH MEMORY



M5M29GB/T320VP (8/16 bit version)



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M5M29GB/T320VP-80

33,554,432-BIT (4,194,304-WORD BY 8-BIT / 2,097,152-WORD BY16-BIT) CMOS 3.3V-ONLY, BLOCK ÉRASE FLASH MEMORÝ

Renesas Technology Corp.

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